

## Description

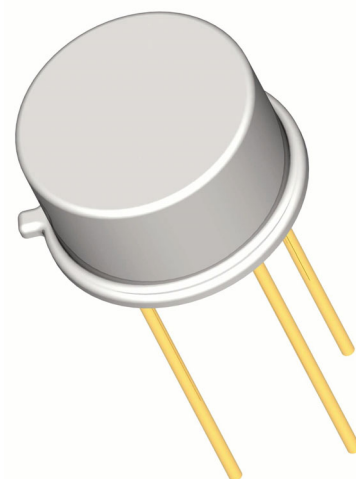
Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N3499LJ)
- JANTX level (2N3499LJX)
- JANTXV level (2N3499LJV)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV
- Radiation testing (total dose) upon request

Please contact Semicoa for special configurations  
[www.SEMICOA.com](http://www.SEMICOA.com) or (714) 979-1900

## Applications

- General purpose
- Low power
- NPN silicon transistor



## Features

- Hermetically sealed TO-5 metal can
- Also available in chip configuration
- Chip geometry 5620
- Reference document: MIL-PRF-19500/366

## Benefits

- Qualification Levels: JAN, JANTX, and JANTXV
- Radiation testing available

Absolute Maximum Ratings		$T_C = 25^{\circ}\text{C}$ unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	Volts
Collector-Base Voltage	$V_{CBO}$	100	Volts
Emitter-Base Voltage	$V_{EBO}$	6	Volts
Collector Current, Continuous	$I_C$	500	mA
Power Dissipation, $T_A = 25^{\circ}\text{C}$ Derate linearly above $25^{\circ}\text{C}$	$P_T$	1 5.71	W mW/ $^{\circ}\text{C}$
Thermal Resistance	$R_{\theta JA}$	175	$^{\circ}\text{C}/\text{W}$
Operating Junction Temperature	$T_J$	-65 to +200	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-65 to +200	$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS

characteristics specified at  $T_A = 25^\circ\text{C}$

Off Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}$	100			Volts
Collector-Base Cutoff Current	$I_{CBO1}$	$V_{CB} = 100\text{ Volts}$			10	$\mu\text{A}$
	$I_{CBO2}$	$V_{CB} = 50\text{ Volts}$			50	nA
	$I_{CBO3}$	$V_{CB} = 50\text{ Volts}, T_A = 150^\circ\text{C}$			50	$\mu\text{A}$
Collector-Emitter Cutoff Current	$I_{CEO}$	$V_{CE} = 80\text{ Volts}$			1	$\mu\text{A}$
Emitter-Base Cutoff Current	$I_{EBO1}$	$V_{EB} = 6\text{ Volts}$			10	$\mu\text{A}$
	$I_{EBO2}$	$V_{EB} = 4\text{ Volts}$			25	nA
On Characteristics			Pulse Test: Pulse Width = 300 $\mu\text{s}$ , Duty Cycle $\leq 2.0\%$			
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{FE1}$	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ Volts}$	35			
	$h_{FE2}$	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ Volts}$	50			
	$h_{FE3}$	$I_C = 10\text{ mA}, V_{CE} = 10\text{ Volts}$	75			
	$h_{FE4}$	$I_C = 150\text{ mA}, V_{CE} = 10\text{ Volts}$	100		300	
	$h_{FE6}$	$I_C = 500\text{ mA}, V_{CE} = 10\text{ Volts}$	20			
	$h_{FE7}$	$I_C = 150\text{ mA}, V_{CE} = 10\text{ Volts}$	45			
		$T_A = -55^\circ\text{C}$				
Base-Emitter Saturation Voltage	$V_{BEsat1}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$			0.8	Volts
	$V_{BEsat3}$	$I_C = 300\text{ mA}, I_B = 30\text{ mA}$			1.4	
Collector-Emitter Saturation Voltage	$V_{CEsat1}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$			0.2	Volts
	$V_{CEsat3}$	$I_C = 300\text{ mA}, I_B = 30\text{ mA}$			0.6	
Dynamic Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE} $	$V_{CE} = 20\text{ Volts}, I_C = 20\text{ mA}, f = 100\text{ MHz}$	1.5		8	
Small Signal Short Circuit Forward Current Transfer Ratio	$h_{FE}$	$V_{CE} = 10\text{ Volts}, I_C = 10\text{ mA}, f = 1\text{ kHz}$	75		375	
Open Circuit Output Capacitance	$C_{OBO}$	$V_{CB} = 10\text{ Volts}, I_E = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			10	pF
Open Circuit Input Capacitance	$C_{IBO}$	$V_{EB} = 0.5\text{ Volts}, I_C = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			80	pF
Noise Figure	$NF_1$	$V_{CE} = 10\text{ Volts}, I_C = 0.5\text{ mA}, f = 1\text{ kHz}, R_g = 1\text{ k}\Omega$			16	dB
	$NF_2$	$V_{CE} = 10\text{ Volts}, I_C = 0.5\text{ mA}, f = 10\text{ kHz}, R_g = 1\text{ k}\Omega$			6	
Switching Characteristics						
Saturated Turn-On Time	$t_{ON}$	$V_{EB} = 5\text{ Volts}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$			1,150	ns
Saturated Turn-Off Time	$t_{OFF}$	$I_C = 150\text{ mA}, I_{B1}=I_{B2}=15\text{ mA}$			115	ns